

RB160SS-40

Silicon Epitaxial Planar Schottky Barrier Diode

Features

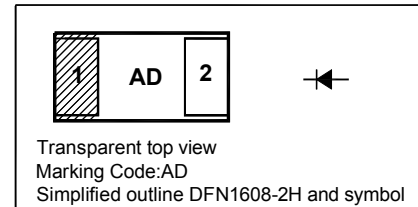
- High reliability
- Low leakage current

Application

- Small current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	$I_{F(AV)}$	1	A
Peak Forward Surge Current (8.3 ms)	I_{FSM}	5	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150	$^\circ\text{C}$

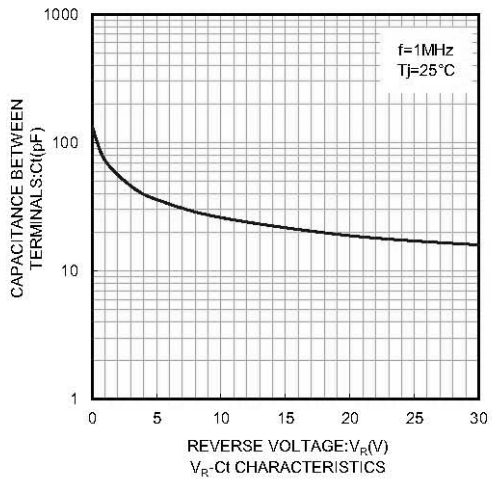
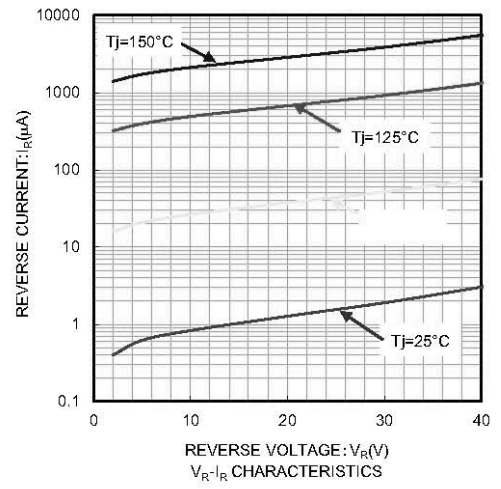
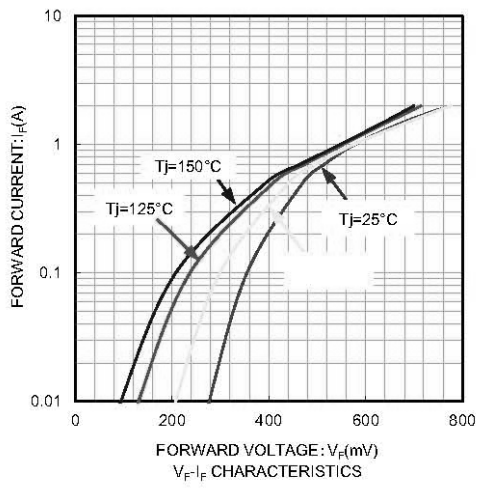
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.7 \text{ A}$	V_F	0.55	V
Reverse Current at $V_R = 40 \text{ V}$	I_R	50	μA

TOP DYNAMIC



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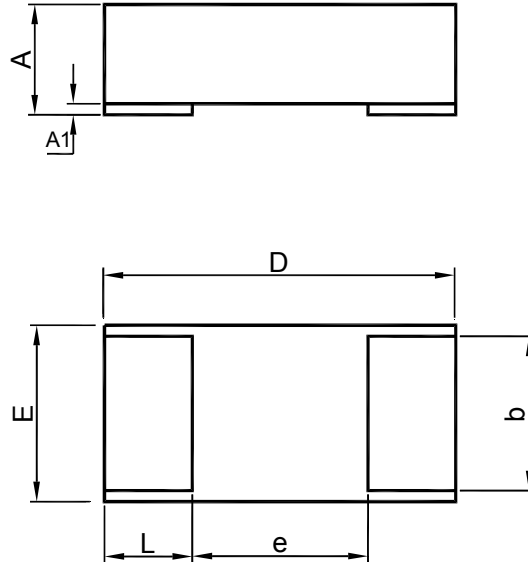


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PACKAGE OUTLINE

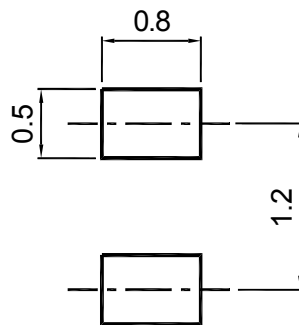
Plastic surface mounted package; 2 leads

DFN1608-2H



UNIT	A	A1	b	D	E	e	L
mm	0.55 0.45	0.05 0	0.75 0.65	1.65 1.55	0.85 0.75	0.85 0.75	0.45 0.35

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1608	8	4 ± 0.1	0.157 ± 0.004	178	7	4,000

TOP DYNAMIC



Dated: 23/05/2014 Rev: 02